VRW0;< ṂṂ Ŀ QSQ ӕṀ ɥ s ǁ Ղ Silicon NPN transistor in a SOT-89 Plastic Package.

ت ᵓ я ں Ḩ ı ɔ ╙ ≹ ı ṅ ғ β
Low $V_{CE(sat)}$, high current, HF Product.

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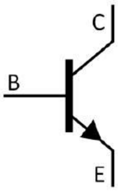
General purpose switching and muting, LCD back-lighting, supply line switching circuits.

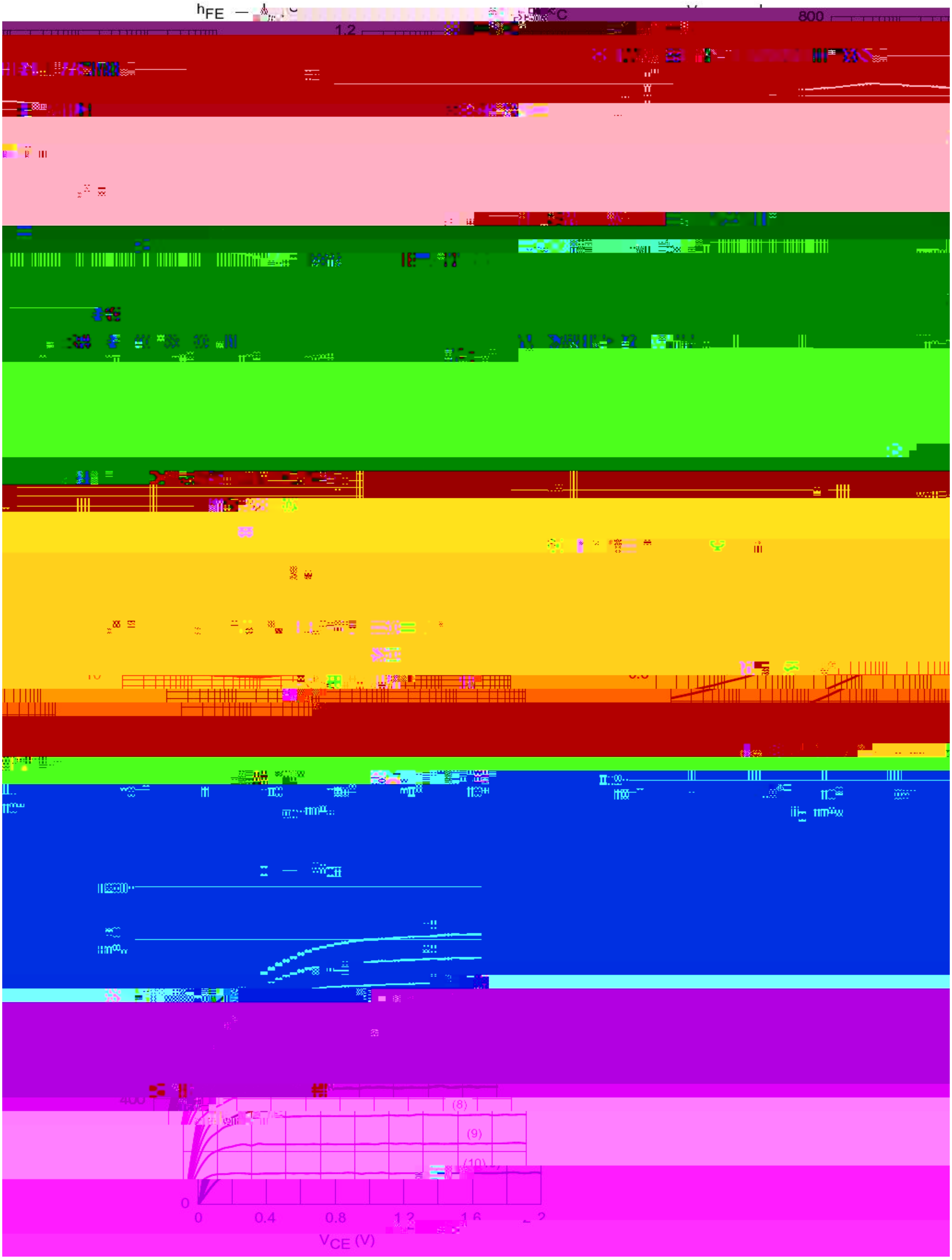


v ̋Ω̣ Parameter	ɬ ᴺ Symbol	̋Ω̣Ӫ Rating	ᴅ ɟ Unit
Collector to Base Voltage	V_{CBO}	50	V
Collector to Emitter Voltage	V_{CEO}	50	V
Emitter to Base Voltage	V_{EBO}	5	V
Collector Current - Continuous	I_C	3	A
Collector Base - Continuous	I_B	0.5	A
Peak Collector Current	I_{CM}	5	A
Total Power Dissipation	P_{tot} ├ 4	550	mW
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-65 150	

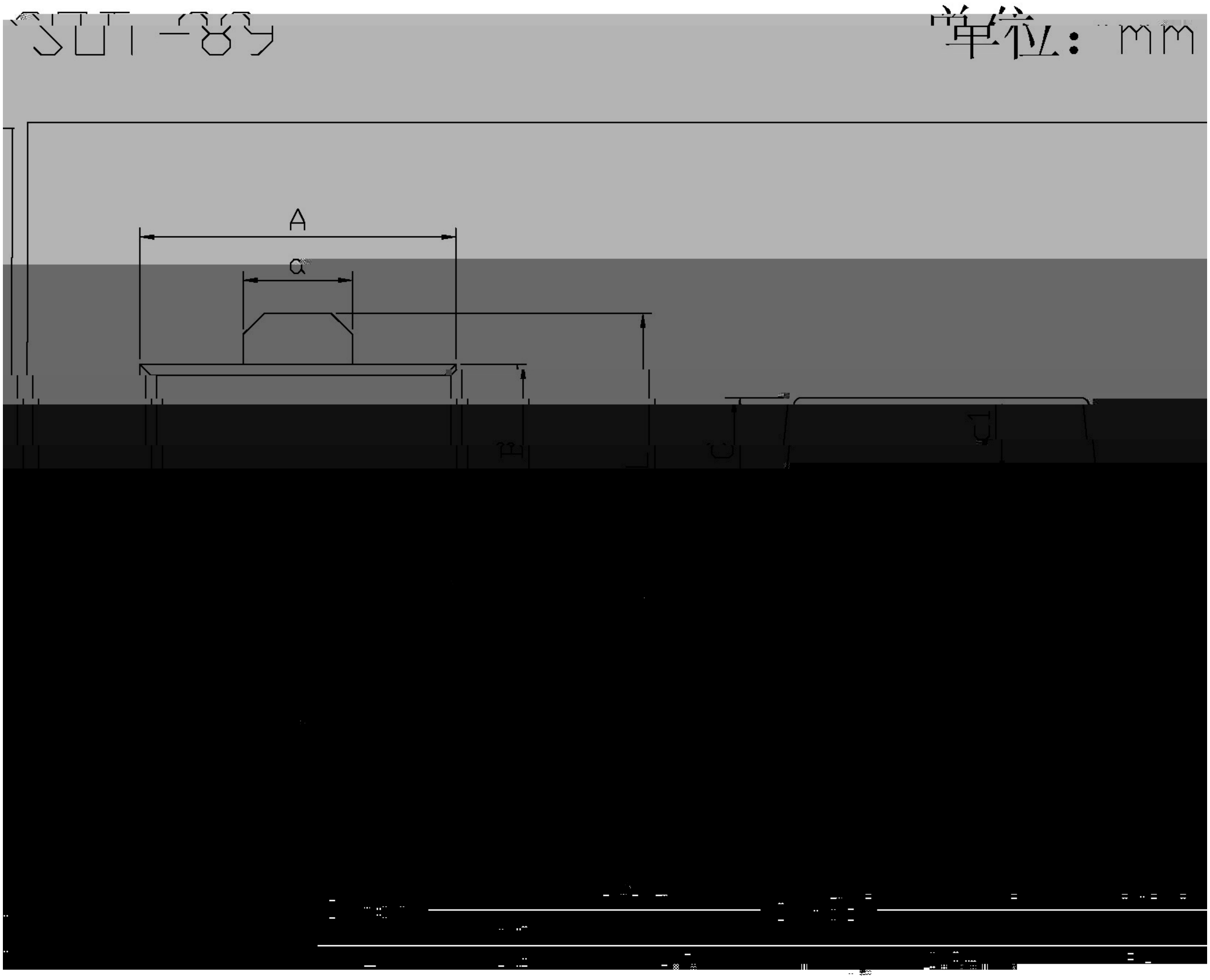
4 λ ᴴ ƫ Ḡ Ł ꞵ ᴍ ͇ ɔ ث— i

v ̋Ω̣ Parameter	ɬ ᴺ Symbol	╜ ؛ᛚ ƫ Test Conditions	ῳ ṇ Ӫ Min	Ɛ ʓ Ӫ Typ	ῳ ᶻ Ӫ Max	ᴅ ɟ Unit
Collector Cut-Off Current	I_{CBO}	V_{CB}=50V I_E=0			100	nA
Collector Cut-Off Current	I_{CBO}	V_{CB}=50V I_E=0 T_j=150			50	A
Collector Cut-Off Current	I_{CES}	V_{CE}=50V V_{BE}=0			100	nA
Emitter Base Cut-Off Current	I_{EBO}	V_{EB}=5.0V I_C=0			100	nA
DC Current Gain	$h_{FE(1)}$	V_{CE}=2.0V I_C=0.1A	300			
	$h_{FE(2)}$	V_{CE}=2.0V I_C=0.5A	300			
	$h_{FE(3)}$*	V_{CE}=2.0V I_C=1.0A	300		700	

/ Electrical Characteristic Curve



/ Package Dimensions



( ) / Temperature Profile for IR Reflow Soldering(Pb-Free)

ب ˝ χ
1 ἱ ♬ □ ŷ 150 Ḱ 180 ɫ ı ˋH ڗ 60 Ḱ 90sec;
2 Š Ө □ ŷ 245 ° 5 ɫ ı ˋH ڗ ˈY ᛰ 㸁 5 ° 0.5sec;
3 ì ˙ Ꮧ ˛ ɔ ൿ ŷ 㸁 2 Ḱ 10 ɫ /sec.

Note:
1.Preheating:150~180 ɫ , Time:60~90sec.
2.Peak Temp.:245 ° 5 ɫ , Duration:5 ° 0.5sec.
3. Cooling Speed: 2~10 ɫ /sec.

/ Resistance to Soldering Heat Test Conditions

□ ŷ χ 260 ° 5 ɫ ˋH ڗ χ 10 ° 1 sec. Temp.:260±5 Time:10±1 sec

/ Packaging SPEC.

ก ˋ γ ㄴ / REEL

Package Type	Units	Dimension (unit mm^3)